



## FDMS3662

### N-Channel Power Trench® MOSFET

100V, 49A, 14.8mΩ

#### Features

- Max  $r_{DS(on)}$  = 14.8mΩ at  $V_{GS} = 10V$ ,  $I_D = 8.9A$
- Advanced Package and Silicon combination for low  $r_{DS(on)}$
- MSL1 robust package design
- 100% UIL Tested
- RoHS Compliant

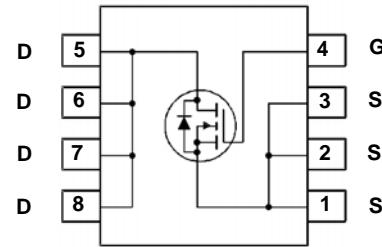
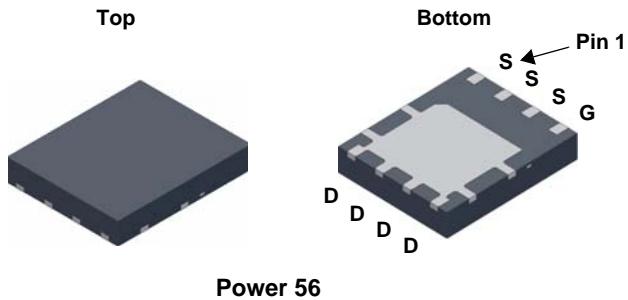


#### General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

#### Application

- DC - DC Conversion



#### MOSFET Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	100	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous (Package limited) $T_C = 25^\circ C$	49	A
	-Continuous (Silicon limited) $T_C = 25^\circ C$	57	
	-Continuous $T_A = 25^\circ C$ (Note 1a)	8.9	
	-Pulsed	90	
$E_{AS}$	Single Pulse Avalanche Energy	(Note 3)	mJ
$P_D$	Power Dissipation $T_C = 25^\circ C$	104	W
	Power Dissipation $T_A = 25^\circ C$ (Note 1a)	2.5	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

#### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.2	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

#### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS3662	FDMS3662	Power 56	13"	12mm	3000 units

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$\text{BV}_{\text{DSS}}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	100			V
$\frac{\Delta \text{BV}_{\text{DSS}}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		74		$\text{mV/}^\circ\text{C}$
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{V}, V_{DS} = 80\text{V}$ ,			1	$\mu\text{A}$
$I_{\text{GSS}}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			$\pm 100$	nA

**On Characteristics**

$V_{GS(\text{th})}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	2.5	3.5	4.5	V
$\frac{\Delta V_{GS(\text{th})}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		-10.8		$\text{mV/}^\circ\text{C}$
$r_{DS(\text{on})}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 8.9\text{A}$		11.4	14.8	$\text{m}\Omega$
		$V_{GS} = 10\text{V}, I_D = 8.9\text{A}, T_J = 125^\circ\text{C}$		19.0	24.7	
$g_{\text{FS}}$	Forward Transconductance	$V_{DD} = 10\text{V}, I_D = 8.9\text{A}$		37		S

**Dynamic Characteristics**

$C_{\text{iss}}$	Input Capacitance	$V_{DS} = 50\text{V}, V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$		3470	4620	pF
$C_{\text{oss}}$	Output Capacitance			245	325	pF
$C_{\text{rss}}$	Reverse Transfer Capacitance			110	165	pF
$R_g$	Gate Resistance	$f = 1\text{MHz}$		1.4		$\Omega$

**Switching Characteristics**

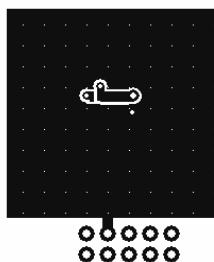
$t_{d(\text{on})}$	Turn-On Delay Time	$V_{DD} = 50\text{V}, I_D = 8.9\text{A}$ , $V_{GS} = 10\text{V}, R_{\text{GEN}} = 6\Omega$		25	40	ns
$t_r$	Rise Time			15	26	ns
$t_{d(\text{off})}$	Turn-Off Delay Time			32	52	ns
$t_f$	Fall Time			6	10	ns
$Q_g$	Total Gate Charge at 10V	$V_{DD} = 50\text{V}$ , $I_D = 8.9\text{A}$		54	75	nC
$Q_{gs}$	Gate to Source Charge			18		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			15		nC

**Drain-Source Diode Characteristics**

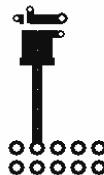
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 8.9\text{A}$ (Note 2)		0.8	1.3	V
		$V_{GS} = 0\text{V}, I_S = 2.1\text{A}$ (Note 2)		0.7	1.2	
$t_{rr}$	Reverse Recovery Time	$I_F = 8.9\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$		45	73	ns
				71	115	nC

## NOTES:

1.  $R_{\text{thJA}}$  is determined with the device mounted on a  $1\text{in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5$  in. board of FR-4 material.  $R_{\text{thJC}}$  is guaranteed by design while  $R_{\text{thCA}}$  is determined by the user's board design.



a.  $50^\circ\text{C}/\text{W}$  when mounted on a  $1\text{in}^2$  pad of 2 oz copper.



b.  $125^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width  $< 300\mu\text{s}$ , Duty cycle  $< 2.0\%$ .

3. Starting  $T_J = 25^\circ\text{C}$ ,  $L = 3\text{mH}$ ,  $I_{AS} = 16\text{A}$ ,  $V_{DD} = 100\text{V}$ ,  $V_{GS} = 10\text{V}$

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

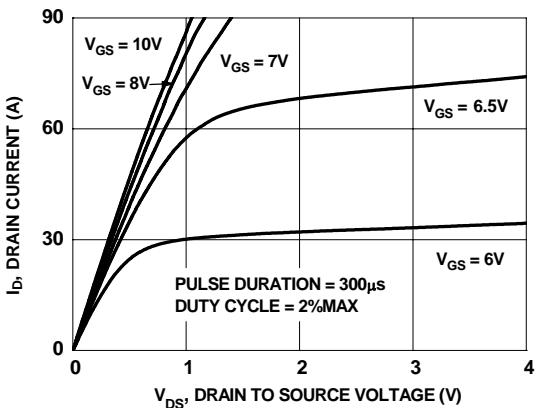


Figure 1. On-Region Characteristics

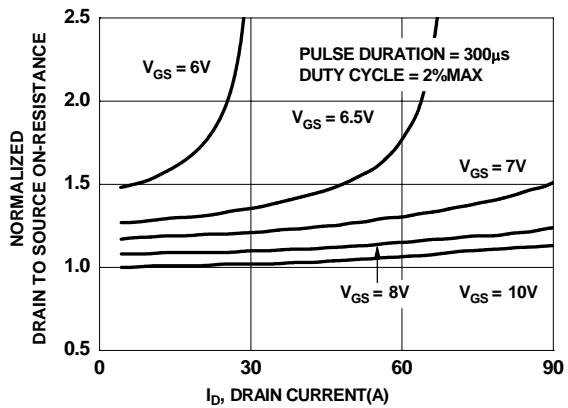


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

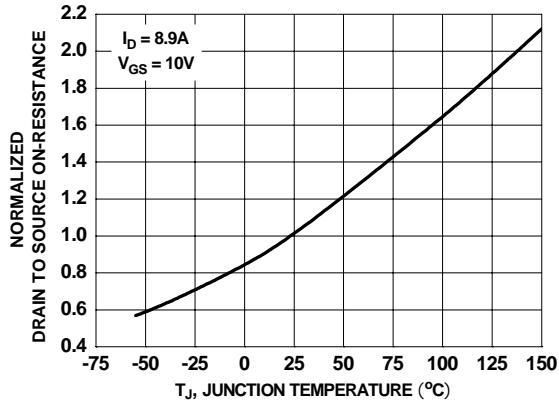


Figure 3. Normalized On-Resistance vs Junction Temperature

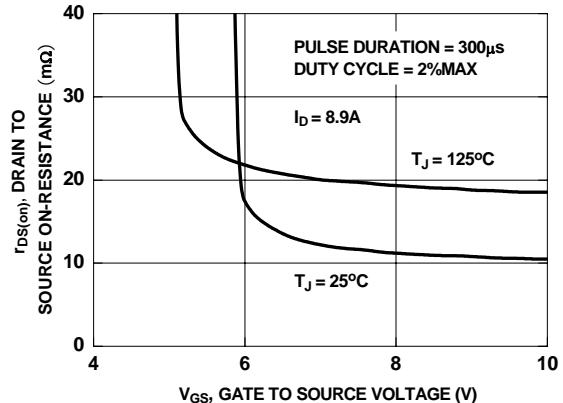


Figure 4. On-Resistance vs Gate to Source Voltage

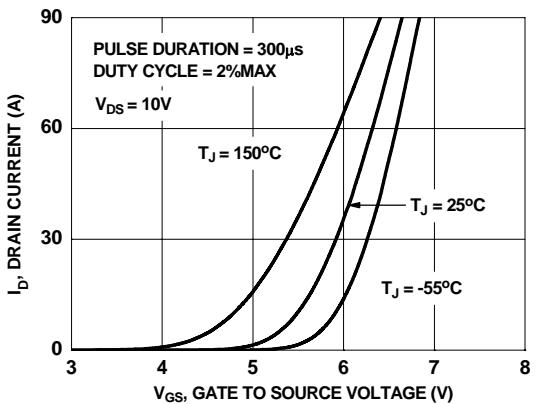


Figure 5. Transfer Characteristics

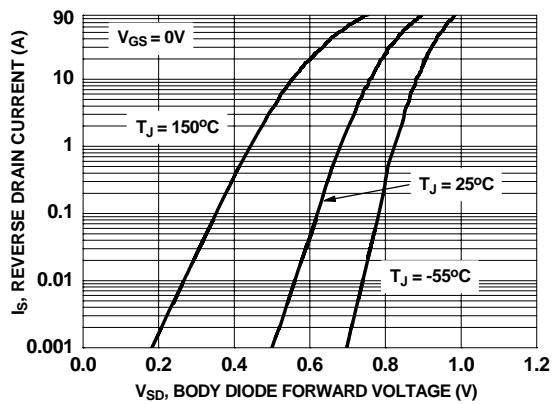


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

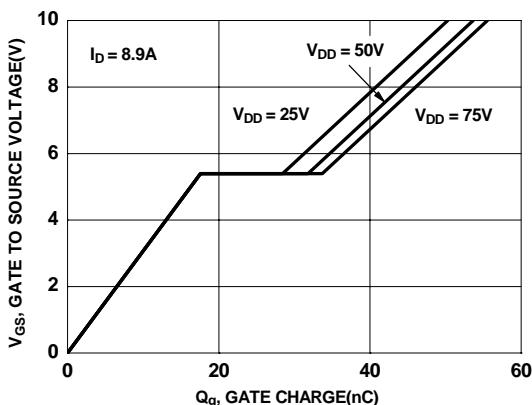


Figure 7. Gate Charge Characteristics

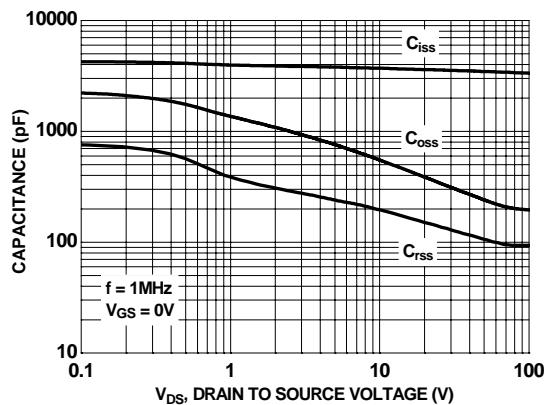


Figure 8. Capacitance vs Drain to Source Voltage

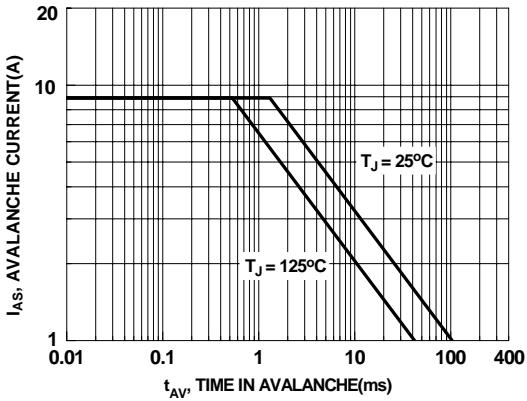


Figure 9. Unclamped Inductive Switching Capability

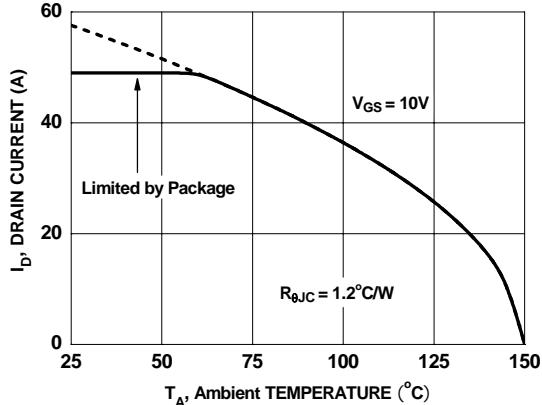


Figure 10. Maximum Continuous Drain Current vs Case Temperature

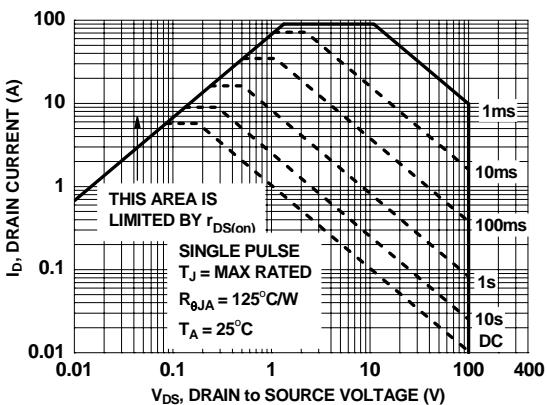


Figure 11. Forward Bias Safe Operating Area

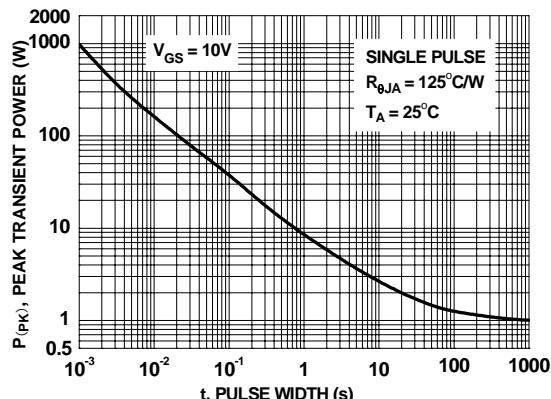
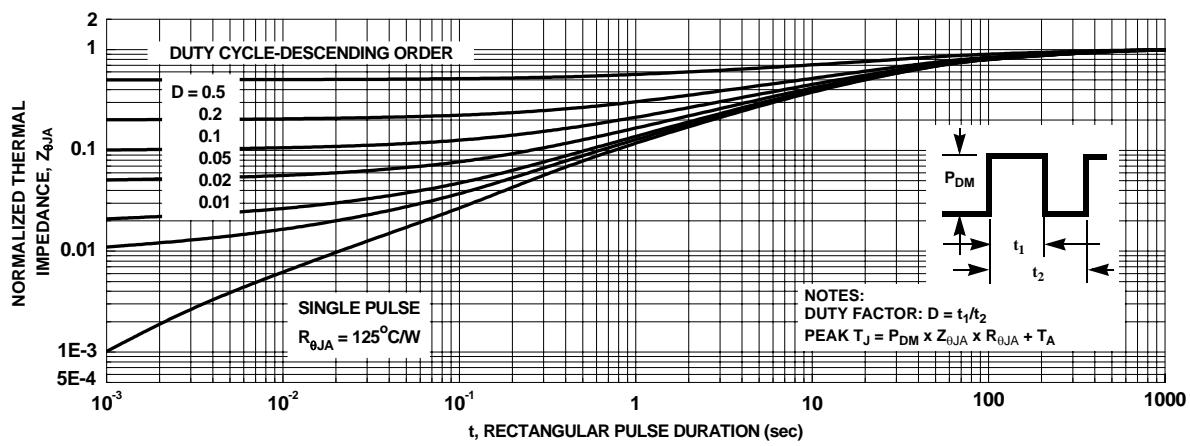
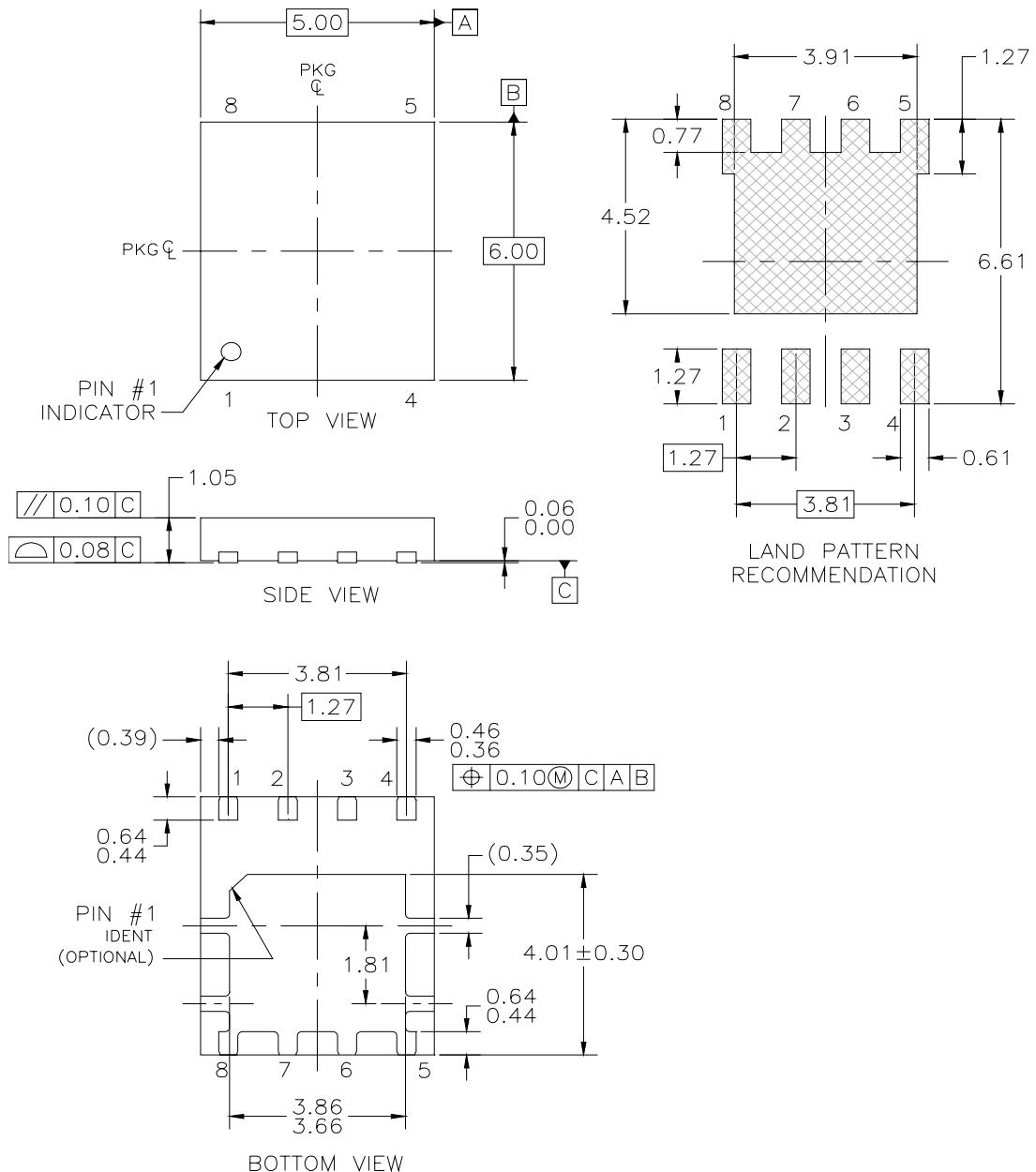


Figure 12. Single Pulse Maximum Power Dissipation

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



**Dimensional Outline and Pad Layout**



NOTES: UNLESS OTHERWISE SPECIFIED

- A) ALL DIMENSIONS ARE IN MILLIMETERS.
- B) NO JEDEC REFERENCE AS OF FEBRUARY 2006
- C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994

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Datasheet Identification	Product Status	Definition
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